

ZXTN04120HFF 120V, SOT23F, NPN medium power Darlington transistor

Summary

BV_{CEO} > 120V

 $I_{C(cont)} = 1A$

V_{CE(sat)} < 1.5V @ 1A

 $P_{D} = 1.5W$

Complementary part number ZXTP05120HFF

Description

This high performance NPN Darlington transistor is housed in the small outline SOT23 flat package for applications where space is at a premium.

Features

- Darlington transistor
- 120 volt
- 1 amp continuous rating •
- Small outline surface mount SOT23 flat package

Applications

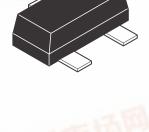
- Lamp, relay and solenoid drive 150.00M
- Lighting

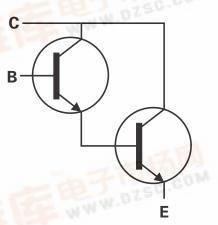
Ordering information

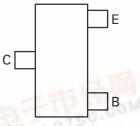
Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN04120HFFTA	7	8	3000
Device marking	BJTP WWW.DZ	SC.COM	

Device marking









Pinout - top view

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	140	V
Collector-emitter voltage	V _{CEO}	120	V
Emitter-base voltage	V _{EBO}	10	V
Continuous collector current (c)	Ι _C	1	А
Peak pulse current	I _{СМ}	4	А
Base current	I _B	0.5	А
Power dissipation @ T _{amb} =25°C ^(a)	PD	0.84	W
Linear derating factor		6.72	mW/°C
Power dissipation @ T _{amb} =25°C ^(b)	PD	1.34	W
Linear derating factor		10.72	mW/°C
Power dissipation @ T _{amb} =25°C ^(c)	PD	1.5	W
Linear derating factor		12.0	mW/°C
Power dissipation @ T _{amb} =25°C ^(d)	PD	2.0	W
Linear derating factor		16.0	mW/°C
Operating and storage temperature range	T _j , T _{stg}	- 55 to 150	°C

Thermal resistance

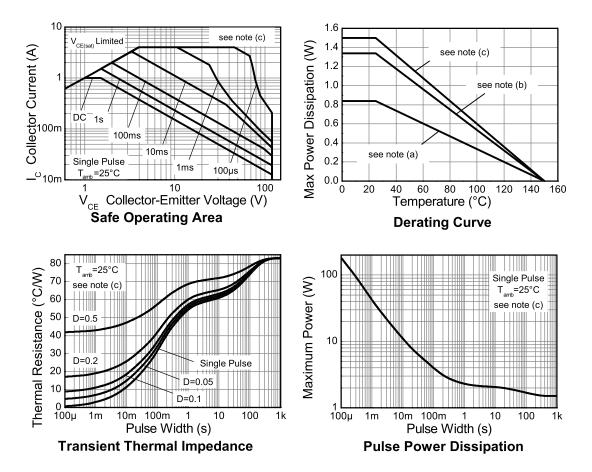
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	149	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	93	°C/W
Junction to ambient ^(c)	$R_{\Theta JA}$	83	°C/W
Junction to ambient ^(d)	$R_{\Theta JA}$	60	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2oz copper in still air conditions.
(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2oz copper in still air conditions.
(d) As (c) above measured at t<5secs.

Characteristics

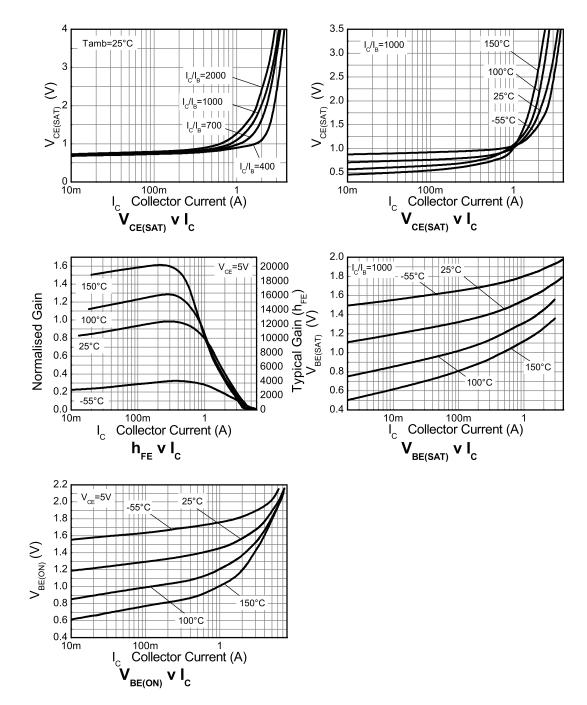


Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	140	300		V	I _C = 100μA
Collector-emitter breakdown voltage (base open)	BV _{CEO}	120	140		V	I _C = 10mA ^(*)
Emitter-base breakdown voltage	BV _{EBO}	10	16		V	I _E = 100μA
Collector-base cut-off current	I _{CBO}		<1	100 10	nA μA	V _{CB} = 120V V _{CB} = 120V, T _{amb} = 100°C
Collector-emitter cut-off current	I _{CES}		<0.1	10	μA	V _{CE} = 120V
Emitter-base cut-off current	I _{EBO}		<1	100	nA	V _{EB} = 8V
Collector-emitter saturation	V _{CE(sat)}		0.8	0.9	V	$I_{\rm C} = 250 {\rm mA}, I_{\rm B} = 0.25 {\rm mA}^{(*)}$
voltage			1.1	1.5	V	I _C = 1A, I _B = 1mA ^(*)
			1.1	1.5	V	I _C = 2A, I _B = 5mA ^(*)
Base-emitter saturation voltage	V _{BE(sat)}		1.55	1.70	V	$I_{\rm C} = 1$ A, $I_{\rm B} = 1$ mA ^(*)
Base-emitter turn-on voltage	V _{BE(on)}		1.45	1.70	V	$I_{C} = 1A, V_{CE} = 5V^{(*)}$
Static forward current	h _{FE}	ЗK	11k			I _C = 50mA, V _{CE} = 5V ^(*)
transfer ratio		ЗК	12k			I _C = 500mA, V _{CE} = 5V ^(*)
		ЗК	10k	30K		$I_{C} = 1A, V_{CE} = 5V^{(*)}$
		1K	5k			$I_{C} = 2A, V_{CE} = 5V^{(*)}$
Transition frequency	f _T		120		MHz	I _C = 100mA, V _{CE} = 10V f = 20MHz
Input capacitance	C _{ibo}		68	90	pF	V _{EB} = 500mV, f = 1MHz ^(*)
Output capacitance	C _{obo}		12.8	25	pF	V _{CB} = 10V, f = 1MHz ^(*)
Delay time	t _d		507		ns	V _{CC} = 10V
Rise time	t _r		136		ns	$I_{\rm C} = 500 {\rm mA},$
Storage time	t _s		910		ns	$I_{B1} = I_{B2} = 0.5 \text{mA}$
Fall time	t _f		369		ns	

NOTES:

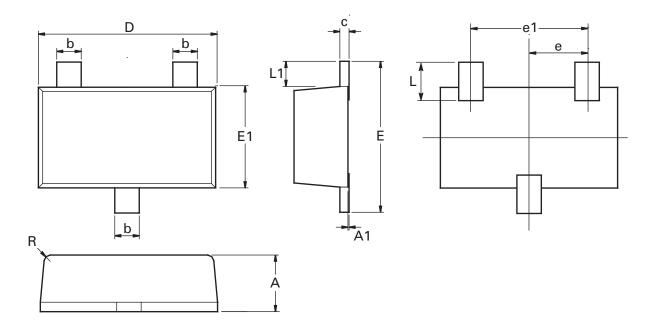
(*) Measured under pulsed conditions. Pulse width ${\leq}300\mu s;$ duty cycle ${\leq}2\%.$



Typical characteristics

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Package outline - SOT23F



Dim.	Millim	neters	Inc	hes	Dim.	n. Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.80	1.00	0.0315	0.0394	E	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	L	0.48	0.68	0.0189	0.0268
С	0.10	0.20	0.0043	0.0079	L1	0.30	0.50	0.0153	0.0161
D	2.80	3.00	0.1102	0.1181	R	0.05	0.15	0.0019	0.0059
е	0.95	ref	0.037	74 ref	0	0°	12°	0°	12°
e1	1.80	2.00	0.0709	0.0787	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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